

Ultra-small P-channel Enhancement-Mode Power MOSFETs

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Advanced Power Electronics has launched a new P-channel Enhancement-mode Power MOSFET, the AP2325GEU6-HF-3, which is well-suited for use in applications such as load switches.

Combining fast switching, low on-resistance and cost-effectiveness, the AP2325GEU6-HF-3 is simple to use and has a low gate charge. It features a minimum Drain-Source Breakdown Voltage (BV_{DSS}) of -20V, maximum R_{DS} (ON) of 145mohms, and a maximum Continuous Drain Current (I_D) at 25degC of -1.8A.

For more information, visit www.a-powerusa.com [1].

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[1] <http://www.a-powerusa.com>